

FUJI POWER MOSFET

Super FAP-G Series

N-CHANNEL SILICON POWER MOSFET

Features

- High speed switching
- Low on-resistance
- No secondary breakdown
- Low driving power
- Avalanche-proof

Applications

- Switching regulators
- UPS (Uninterruptible Power Supply)
- DC-DC converters

Maximum ratings and characteristic Absolute maximum ratings

● (T_c=25°C unless otherwise specified)

Item	Symbol	Ratings	Unit
Drain-source voltage	V _{DS}	900	V
	V _{DSX} *5	900	V
Continuous drain current	I _D	±9	A
Pulsed drain current	I _D (puls)	±36	A
Gate-source voltage	V _{GS}	±30	V
Repetitive or non-repetitive	I _{AR} *2	9	A
Maximum Avalanche Energy	E _{AS} *1	287.7	mJ
Maximum Drain-Source dV/dt	dV _{DS} /dt *4	40	kV/μs
Peak Diode Recovery dV/dt	dV/dt *3	5	kV/μs
Max. power dissipation	P _D	T _a =25°C	2.02
		T _c =25°C	270
Operating and storage temperature range	T _{ch}	+150	°C
	T _{stg}	-55 to +150	°C

*1 L=6.51mH, V_{CC}=90V, T_{ch}=25°C See to Avalanche Energy Graph *2 T_{ch}≤150°C

*3 I_F≤-I_D, -di/dt=50A/μs, V_{CC}≤BV_{DSS}, T_{ch}≤150°C *4 V_{DS}≤900V *5 V_{GS}=-30V

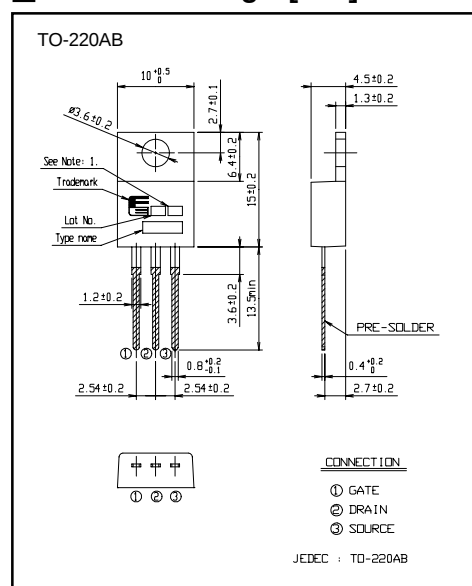
Electrical characteristics (T_c=25°C unless otherwise specified)

Item	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Drain-source breakdown voltage	V _{(BR)DSS}	I _D =250μA V _{GS} =0V	900			V
Gate threshold voltage	V _{GS(th)}	I _D =250μA V _{DS} =V _{GS}	3.0		5.0	V
Zero gate voltage drain current	I _{DSS}	V _{DS} =900V V _{GS} =0V			25	μA
		V _{DS} =720V V _{GS} =0V			250	
Gate-source leakage current	I _{GSS}	V _{GS} =±30V V _{DS} =0V			100	nA
Drain-source on-state resistance	R _{DS(on)}	I _D =4.5A V _{GS} =10V		1.22	1.58	Ω
Forward transconductance	g _{fs}	I _D =4.5A V _{DS} =25V	5	10		S
Input capacitance	C _{iss}	V _{DS} =25V		1100	1650	pF
Output capacitance	C _{oss}	V _{GS} =0V		140	210	
Reverse transfer capacitance	C _{rss}	f=1MHz		8	12	
Turn-on time t _{on}	td(on)	V _{CC} =600V I _D =4.5A		25	38	ns
	t _r	V _{GS} =10V		12	18	
Turn-off time t _{off}	td(off)	R _{GS} =10 Ω		50	75	
	t _f			12	18	
Total Gate Charge	Q _G	V _{CC} =450V		31	46.5	nC
Gate-Source Charge	Q _{GS}	I _D =9A		4.5	8	
Gate-Drain Charge	Q _{GD}	V _{GS} =10V		11	16.5	
Avalanche capability	I _{AV}	L=6.51mH T _{ch} =25°C	9			A
Diode forward on-voltage	V _{SD}	I _F =9A V _{GS} =0V T _{ch} =25°C		0.90	1.50	V
Reverse recovery time	t _{rr}	I _F =9A V _{GS} =0V		3.2		μs
Reverse recovery charge	Q _{rr}	-di/dt=100A/μs T _{ch} =25°C		15.5		μC

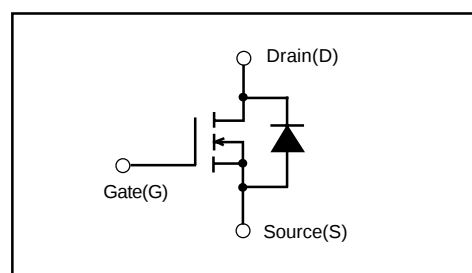
Thermal characteristics

Item	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Thermal resistance	R _{th(ch-c)}	channel to case			0.463	°C/W
	R _{th(ch-a)}	channel to ambient			62.0	°C/W

Outline Drawings [mm]

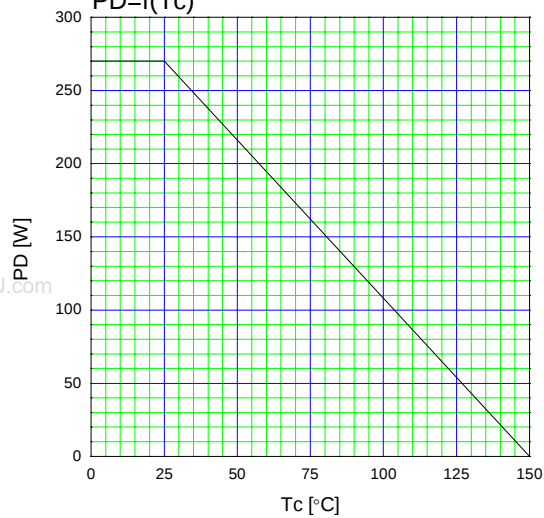


Equivalent circuit schematic

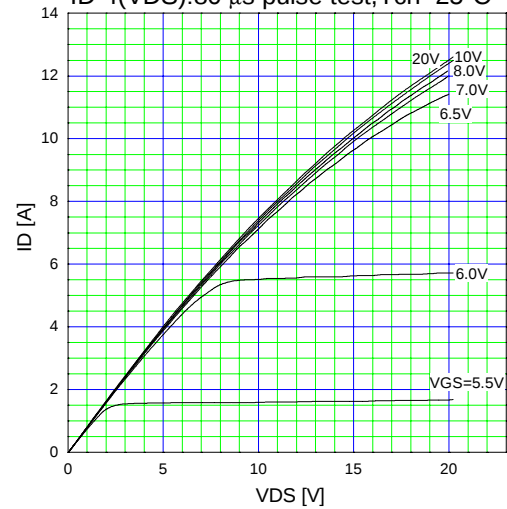


Characteristics

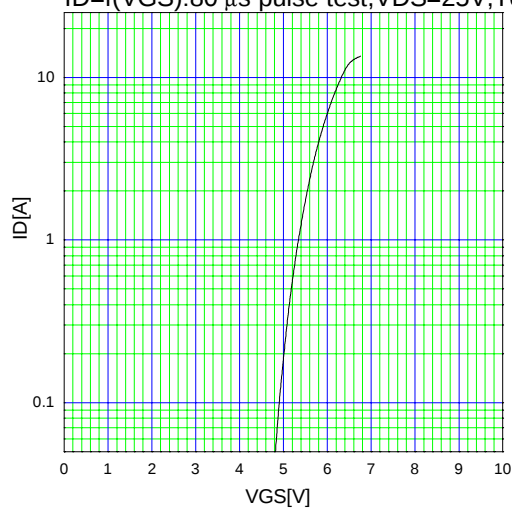
Allowable Power Dissipation
 $PD=f(T_c)$



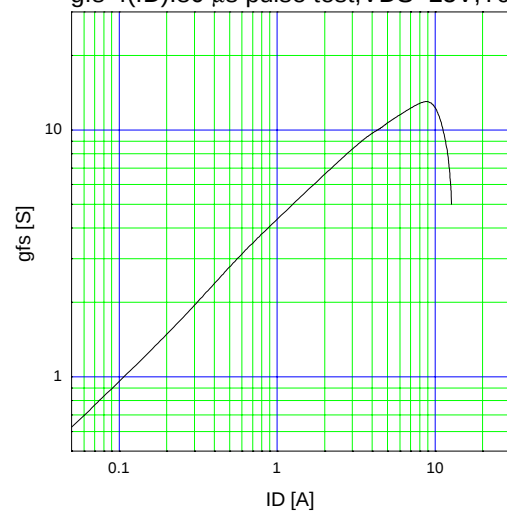
Typical Output Characteristics
 $ID=f(V_{DS}): 80 \mu s$ pulse test, $T_{ch}=25^{\circ}C$



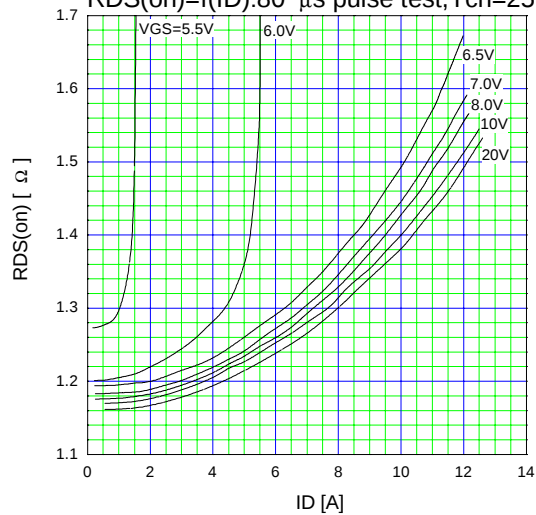
Typical Transfer Characteristic
 $ID=f(V_{GS}): 80 \mu s$ pulse test, $V_{DS}=25V$, $T_{ch}=25^{\circ}C$



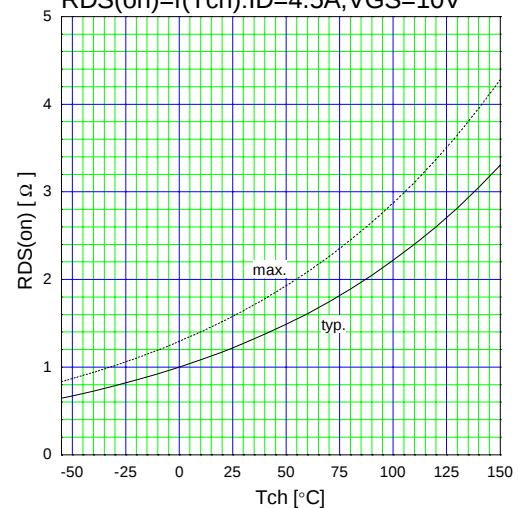
Typical Transconductance
 $g_{fs}=f(ID): 80 \mu s$ pulse test, $V_{DS}=25V$, $T_{ch}=25^{\circ}C$



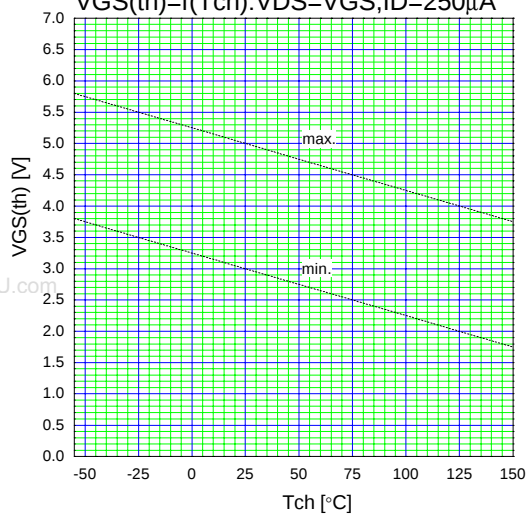
Typical Drain-Source on-state Resistance
 $R_{DS(on)}=f(ID): 80 \mu s$ pulse test, $T_{ch}=25^{\circ}C$



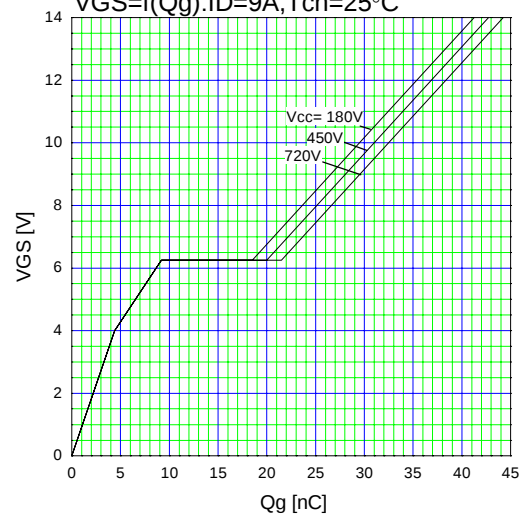
Drain-Source On-state Resistance
 $R_{DS(on)}=f(T_{ch}): ID=4.5A$, $V_{GS}=10V$



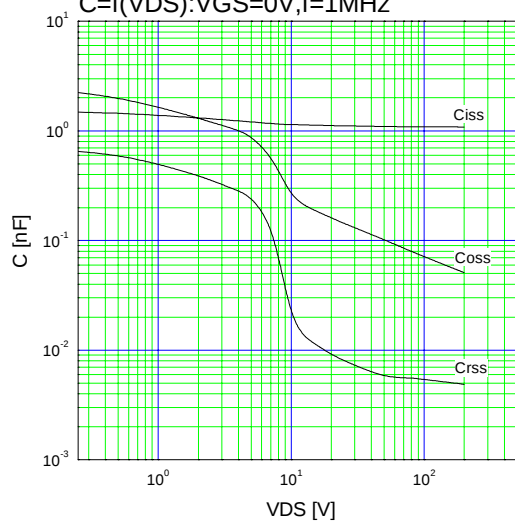
Gate Threshold Voltage vs. T_{ch}
 $V_{GS(th)} = f(T_{ch}) : V_{DS} = V_{GS}, I_D = 250 \mu A$



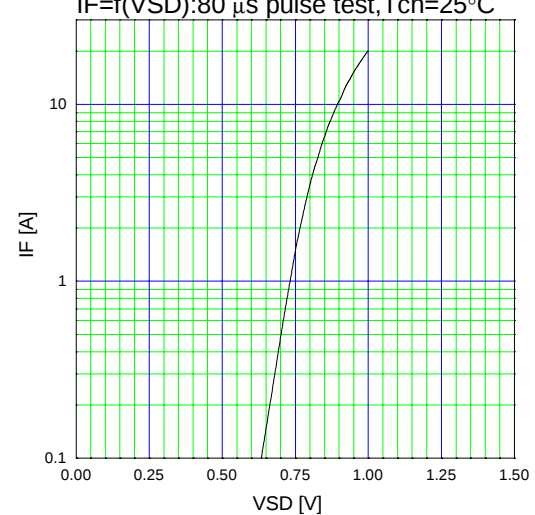
Typical Gate Charge Characteristics
 $V_{GS} = f(Q_g) : I_D = 9A, T_{ch} = 25^\circ C$



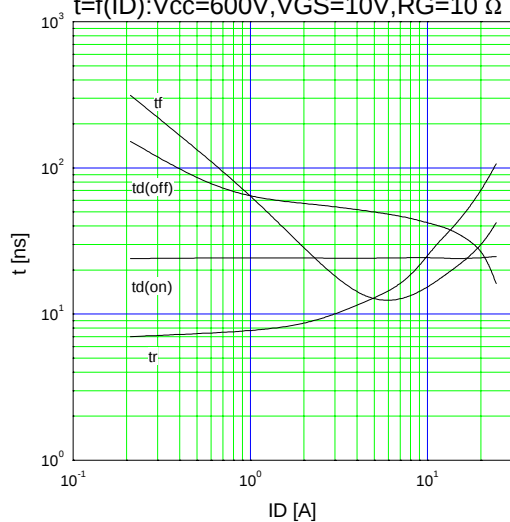
Typical Capacitance
 $C = f(V_{DS}) : V_{GS} = 0V, f = 1MHz$



Typical Forward Characteristics of Reverse Diode
 $I_F = f(V_{SD}) : 80 \mu s \text{ pulse test}, T_{ch} = 25^\circ C$



Typical Switching Characteristics vs. I_D
 $t = f(I_D) : V_{CC} = 600V, V_{GS} = 10V, R_G = 10 \Omega$



Maximum Avalanche Energy vs. starting T_{ch}
 $E_{AS} = f(\text{starting } T_{ch}) : V_{CC} = 90V$

